

1200V Wide-Bandgap SiC Schottky Diodes

New 1200V Wide Bandgap Silicon Carbide (SiC) Schottky diodes feature a merged PIN Schottky (MPS) structure, delivering outstanding performance with high forward surge current capability, low forward voltage drop, low leakage current, and low capacitive charge.

Available in 1A and 2A current ratings in compact SMB and low-profile SOD-128 packages, these diodes provide improved creepage distances (e.g., 3.2mm for SOD-128, 2.6mm for SMB) to ensure better electrical isolation. For higher current demands, versions rated up to 40A are offered in TO-247-3L packages, enabling system-level optimization across a wide range of power designs.



Official Website



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LinkedIn

For more information: marketing@ts.com.tw

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PACKAGE



SOD-128



DO-214AA (SMB)



TO-247-2L



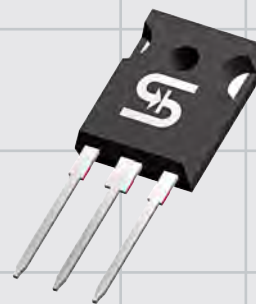
TO-220AC-2L



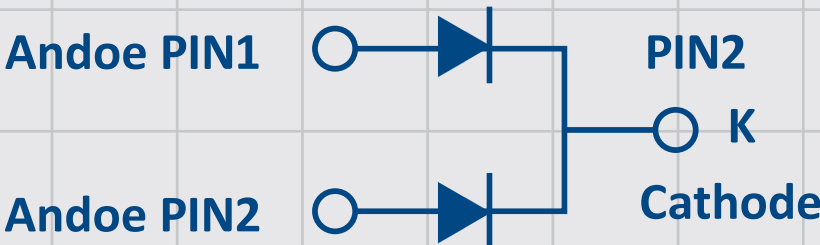
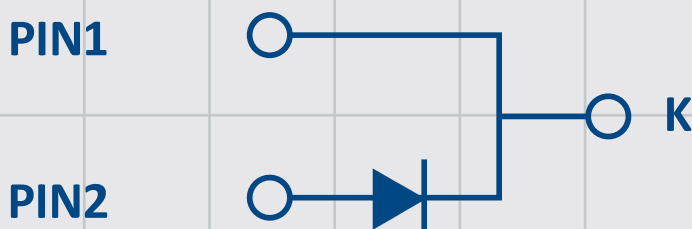
TO-252-2L



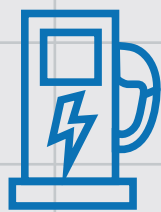
TO-263-2L



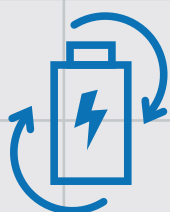
TO-247-3L



APPLICATIONS



EV FAST CHARGING STATIONS



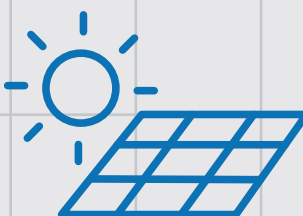
GRID ENERGY STORAGE SYSTEM (ESSs)



UNINTERRUPTIBLE POWER SUPPLIES (UPS)



TELECOM RECTIFIERS

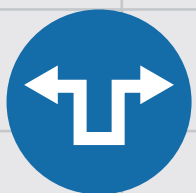


SOLAR INVERTER SYSTEMS

FEATURES



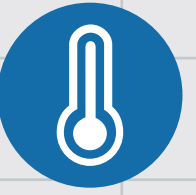
POSITIVE TEMPERATURE COEFFICIENT ON V_F



SOD-128 MINIMUM CREEPAGE DISTANCE
3.2mm GUARANTEED BY DESIGN

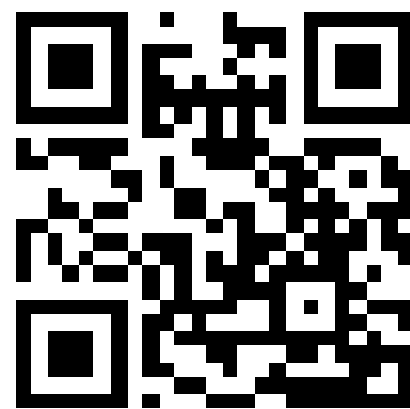


AUTOMOTIVE QUALIFIED
AEC-Q101



T_j max, up to
175°C

SPECIFICATION



Scan or click QR code for specification



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